# HF / VHF power LDMOS transistor

**AMPLEON** 

Rev. 1 — 3 April 2020

Product data sheet

# 1. Product profile

#### 1.1 General description

A 1200 W LDMOS power transistor for broadcast applications and industrial applications in the HF to 700 MHz band.

Table 1. Application information

Test signal	f	V <sub>DS</sub>	PL	Gp	η <sub>D</sub>
	(MHz)	(V)	(W)	(dB)	(%)
CW pulsed [1]	225	50	1200	25.5	80.0
CW pulsed [2]	352	50	1150	25.0	79.6
CW [2]	352	50	1150	23.6	76.7
CW [3]	500	45	800	22.3	71.6
CW [4]	650	50	1000	20.0	66.2

<sup>[1]</sup> On production test circuit  $t_p$  = 100  $\mu$ s;  $\delta$  = 10 %.

### 1.2 Features and benefits

- Easy power control
- Integrated ESD protection
- Excellent ruggedness
- High efficiency
- Excellent thermal stability
- Designed for broadband operation (10 MHz to 700 MHz)
- For RoHS compliance see the product details on the Ampleon website

# 1.3 Applications

- Industrial, scientific and medical applications
- Broadcast transmitter applications

<sup>[2]</sup> AR191160.

<sup>[3]</sup> AR191195.

<sup>[4]</sup> AR201049.

#### **HF / VHF power LDMOS transistor**

# 2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	drain1		
2	drain2	1 2	اً ا
3	gate1	5	3_
4	gate2	3 4	5
5	source	[1]	4 7
			, ' <u></u>
			2 sym117

[1] Connected to flange.

# 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BLF978P	-	flanged balanced ceramic package; 2 mounting holes; 4 leads	SOT539A

# 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage		-	108	V
$V_{GS}$	gate-source voltage		-6	+11	V
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature	[1]	-	225	°C

<sup>[1]</sup> Continuous use at maximum temperature will affect the reliability, for details refer to the online MTF calculator.

## 5. Thermal characteristics

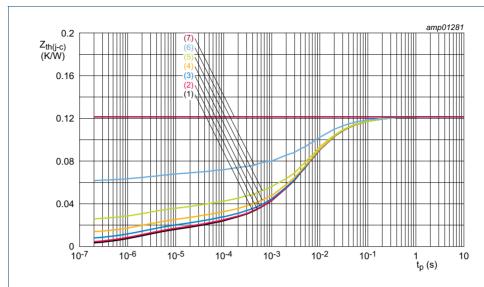
Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
R <sub>th(j-c)</sub>	thermal resistance from junction to case	$T_{case} = 90  ^{\circ}C$	0.121	K/W
Z <sub>th(j-c)</sub>	transient thermal impedance from junction to case	$T_{case} = 90  ^{\circ}\text{C};  t_p = 100  \mu\text{s}; \ \delta = 10  \%$	0.033	K/W

<sup>[1]</sup>  $R_{th(j-c)}$  is measured under RF conditions.

<sup>[2]</sup> See Figure 1.

## HF / VHF power LDMOS transistor



- (1)  $\delta = 1 \%$
- (2)  $\delta = 2 \%$
- (3)  $\delta = 5 \%$
- (4)  $\delta = 10 \%$
- (5)  $\delta = 20 \%$
- (6)  $\delta = 50 \%$
- (7)  $\delta = 100 \% (DC)$

Fig 1. Transient thermal impedance from junction to case as a function of pulse duration

# 6. Characteristics

#### Table 6. DC characteristics

 $T_i = 25$  °C; per section unless otherwise specified.

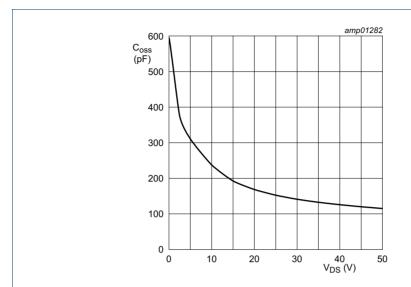
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 3.94 \text{ mA}$	108	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$V_{DS} = 10 \text{ V}; I_D = 394 \text{ mA}$	1.5	2.0	2.5	V
I <sub>DSS</sub>	drain leakage current	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 50 V	-	-	2.8	μΑ
I <sub>DSX</sub>	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	54	71.7	-	Α
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 11 V; V <sub>DS</sub> = 0 V	-	-	280	nA
R <sub>DS(on)</sub>	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 13.79 \text{ A}$	-	54	-	mΩ

#### Table 7. AC characteristics

 $T_i = 25$  °C; per section unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C <sub>rs</sub>	feedback capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}; f = 1 \text{ MHz}$	-	1.45	-	pF
C <sub>iss</sub>	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}; f = 1 \text{ MHz}$	-	392	-	pF
C <sub>oss</sub>	output capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}; f = 1 \text{ MHz}$	-	115	-	pF

## HF / VHF power LDMOS transistor



 $V_{GS} = 0 V$ ; f = 1 MHz.

Fig 2. Output capacitance as a function of drain-source voltage; typical values per section

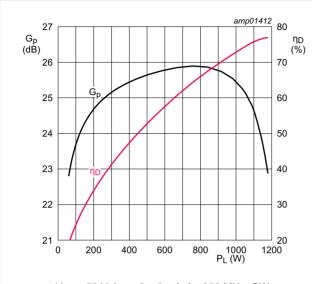
Table 8. RF characteristics

Test signal: CW pulsed;  $t_p$  = 100  $\mu$ s;  $\delta$  = 10 %; f = 225 MHz; RF performance at  $V_{DS}$  = 50 V;  $I_{Dq}$  = 50 mA per section;  $T_{case}$  = 25 °C; unless otherwise specified; in a class-AB production test circuit.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Gp	power gain	P <sub>L</sub> = 1200 W	23	24.5	-	dB
RLin	input return loss	P <sub>L</sub> = 1200 W	-	-20	-12	dB
η <sub>D</sub>	drain efficiency	P <sub>L</sub> = 1200 W	78	80.6	-	%

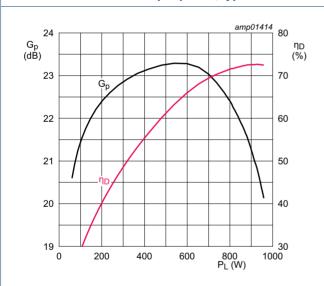
## HF / VHF power LDMOS transistor

# 7. Application information



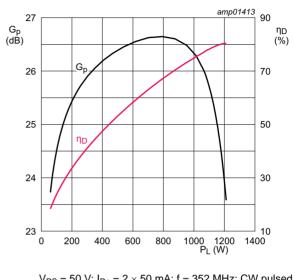
 $V_{DS}$  = 50 V;  $I_{Dq}$  = 2  $\times$  5 mA; f = 352 MHz; CW.

Fig 3. Power gain and drain efficiency on AR191160 as function of output power; typical values



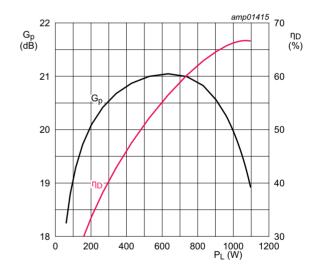
 $V_{DS}$  = 45 V;  $I_{Dq}$  = 2 × 10 mA; f = 500 MHz; CW.

Fig 5. Power gain and drain efficiency on AR191195 as function of output power; typical values



 $V_{DS}$  = 50 V;  $I_{Dq}$  = 2  $\times$  50 mA; f = 352 MHz; CW pulsed (tp = 100  $\mu s;$   $\delta$  = 10 %).

Fig 4. Power gain and drain efficiency on AR191160 as function of output power; typical values



 $V_{DS}$  = 50 V;  $I_{Dq}$  = 2  $\times$  10 mA; f = 650 MHz; CW.

Fig 6. Power gain and drain efficiency on AR201049 as function of output power; typical values

HF / VHF power LDMOS transistor

# 8. Test information

## 8.1 Ruggedness in class-AB operation

The BLF978P is capable of withstanding a load mismatch corresponding to VSWR = 13 : 1 through all phases under the following conditions:  $V_{DS}$  = 50 V;  $I_{Dq}$  = 50 mA per section;  $P_L$  = 1200 W; f = 225 MHz; CW pulsed ( $t_p$  = 100  $\mu$ s;  $\delta$  = 10 %).

## 8.2 Impedance information

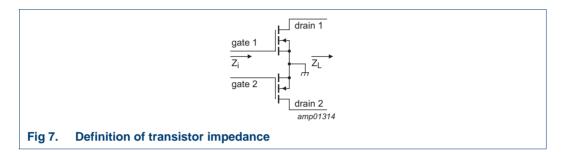


Table 9. Typical push-pull impedance

Simulated  $Z_i$  and  $Z_L$  device impedance; impedance info at  $V_{DS} = 50 \text{ V}$  and  $P_L = 1200 \text{ W}$ .

f	Z <sub>i</sub>	Z <sub>L</sub>
(MHz)	<b>(</b> Ω <b>)</b>	<b>(</b> Ω <b>)</b>
225	1.1 – j4.4	3.7 + j1.1

#### **HF / VHF power LDMOS transistor**

## 8.3 Test circuit

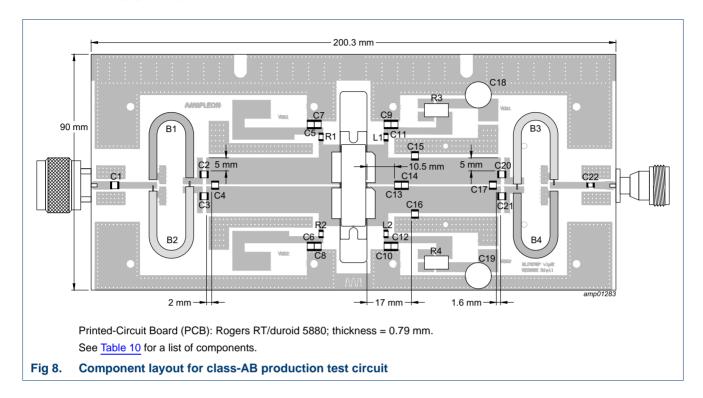


Table 10. List of components

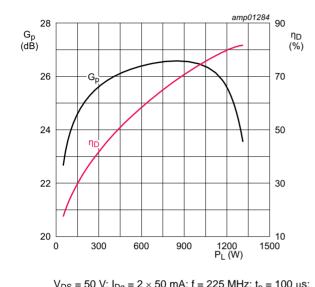
For test circuit see Figure 8.

Component	Description	Value	Remarks
C1, C7, C8, C9, C10, C22	multilayer ceramic chip capacitor	1 nF	ATC 100B
C2, C3	multilayer ceramic chip capacitor	62 pF	ATC 100B
C4	multilayer ceramic chip capacitor	111 pF	ATC 100B
C5, C6, C11, C12	multilayer ceramic chip capacitor	4.7 μF, 100 V	C3225X7S2A475K200AE
C13, C14, C20, C21	multilayer ceramic chip capacitor	47 pF	ATC 100B
C15, C16	multilayer ceramic chip capacitor	43 pF	ATC 100B
C17	multilayer ceramic chip capacitor	51 pF	ATC 100B
C18, C19	electrolytic capacitor	1500 μF, 80 V	
L1, L2	air core inductor	17.5 nH	B06TJLB
R1, R2	SMD resistor	5.1 Ω	SMD 1206
R3, R4	shunt resistor	0.01 Ω	Ohmite: FC4L110R010FER
B1, B2, B3, B4	coaxial line	50 Ω, 58 mm	HUBER+SUHNER: EZ-141-AL-TP-M17

#### **HF / VHF power LDMOS transistor**

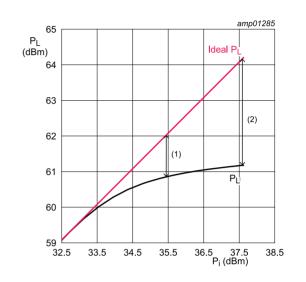
## 8.4 Graphical data

# 8.4.1 1-Tone CW pulsed



 $V_{DS}$  = 50 V;  $I_{Dq}$  = 2  $\times$  50 mA; f = 225 MHz;  $t_p$  = 100  $\mu s;$   $\delta$  = 10 %.

Fig 9. Power gain and drain efficiency as function of output power; typical values

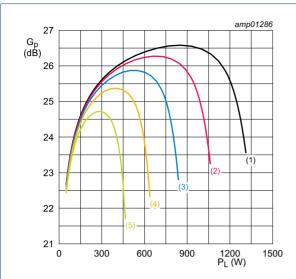


 $V_{DS}$  = 50 V;  $I_{Dq}$  = 2  $\times$  50 mA; f = 225 MHz;  $t_p$  = 100  $\mu s;$   $\delta$  = 10 %.

- (1)  $P_{L(1dB)} = 60.79 \text{ dBm } (1200 \text{ W})$
- (2)  $P_{L(3dB)} = 61.17 \text{ dBm } (1310 \text{ W})$

Fig 10. Output power as a function of input power; typical values

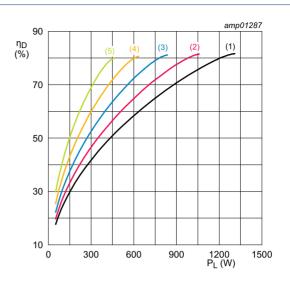
### **HF / VHF power LDMOS transistor**



 $I_{Dq}$  = 2 × 50 mA; f = 225 MHz;  $t_{p}$  = 100  $\mu$ s;  $\delta$  = 10 %.

- (1)  $V_{DS} = 50 \text{ V}$
- (2)  $V_{DS} = 45 \text{ V}$
- (3)  $V_{DS} = 40 \text{ V}$
- (4)  $V_{DS} = 35 \text{ V}$
- (5)  $V_{DS} = 30 \text{ V}$

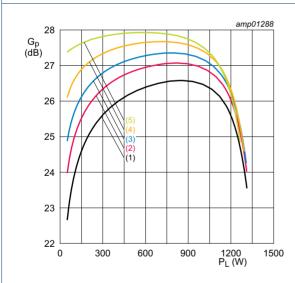
Fig 11. Power gain as a function of output power; typical values



 $I_{Dq} = 2 \times 50$  mA; f = 225 MHz;  $t_p = 100 \mu s$ ;  $\delta = 10 \%$ .

- (1)  $V_{DS} = 50 \text{ V}$
- (2)  $V_{DS} = 45 \text{ V}$
- (3)  $V_{DS} = 40 \text{ V}$
- (4)  $V_{DS} = 35 V$
- (5)  $V_{DS} = 30 \text{ V}$

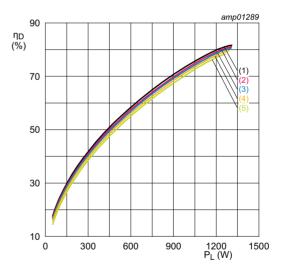
Fig 12. Drain efficiency as a function of output power; typical values



 $V_{DS}$  = 50 V; f = 225 MHz;  $t_p$  = 100  $\mu$ s;  $\delta$  = 10 %.

- (1)  $I_{Dq} = 2 \times 50 \text{ mA}$
- (2)  $I_{Dq} = 2 \times 200 \text{ mA}$
- (3)  $I_{Dq} = 2 \times 400 \text{ mA}$
- (4)  $I_{Dq} = 2 \times 800 \text{ mA}$
- (5)  $I_{Dq} = 2 \times 1400 \text{ mA}$

Fig 13. Power gain as a function of output power; typical values

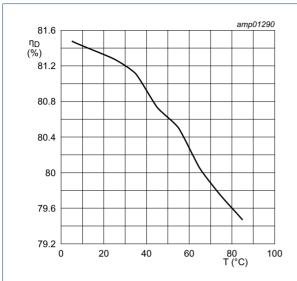


 $V_{DS} = 50 \text{ V}$ ; f = 225 MHz;  $t_p = 100 \text{ }\mu\text{s}$ ;  $\delta = 10 \text{ }\%$ .

- (1)  $I_{Dq} = 2 \times 50 \text{ mA}$
- (2)  $I_{Dq} = 2 \times 200 \text{ mA}$
- (3)  $I_{Dq} = 2 \times 400 \text{ mA}$
- (4)  $I_{Dq} = 2 \times 800 \text{ mA}$
- (5)  $I_{Dq} = 2 \times 1400 \text{ mA}$

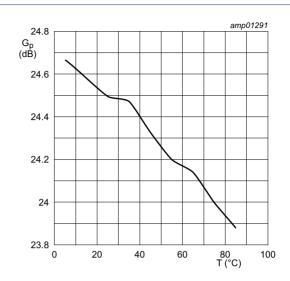
Fig 14. Drain efficiency as a function of output power; typical values

#### **HF / VHF power LDMOS transistor**



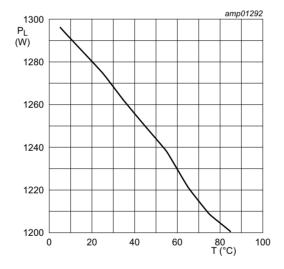
 $V_{DS}$  = 50 V;  $I_{Dq}$  = 2 × 50 mA; f = 225 MHz; at  $P_{L(2dB)}$ .

Fig 15. Drain efficiency as a function of temperature; typical values



 $V_{DS}$  = 50 V;  $I_{Dq}$  = 2 × 50 mA; f = 225 MHz; at  $P_{L(2dB)}$ .

Fig 16. Power gain as a function of temperature; typical values



 $V_{DS} = 50 \text{ V}; I_{Dq} = 2 \times 50 \text{ mA}; f = 225 \text{ MHz}; at P_{L(2dB)}.$ 

Fig 17. Output power as a function of temperature; typical values

# 9. Package outline

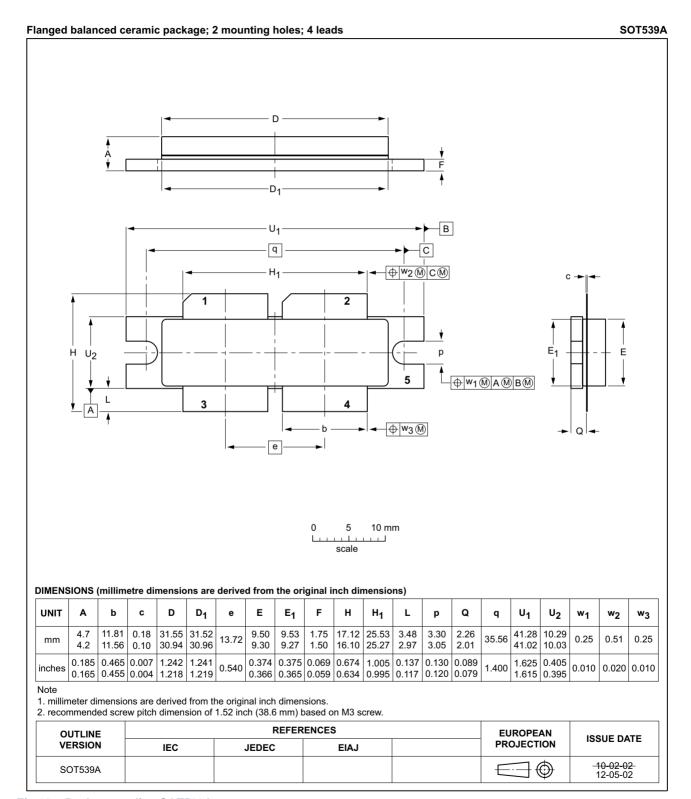


Fig 18. Package outline SOT539A

**AMPLEON** 

#### **HF / VHF power LDMOS transistor**

# 10. Handling information

#### **CAUTION**



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

Table 11. ESD sensitivity

ESD model	Class
Charged Device Model (CDM); According to ANSI/ESDA/JEDEC standard JS-002	C2A [1]
Human Body Model (HBM); According to ANSI/ESDA/JEDEC standard JS-001	2 [2]

- [1] CDM classification C2A is granted to any part that passes after exposure to an ESD pulse of 500 V.
- HBM classification 2 is granted to any part that passes after exposure to an ESD pulse of 2000 V.

## 11. Abbreviations

Table 12. Abbreviations

Acronym	Description
CW	Continuous Wave
HF	High Frequency
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
MTF	Median Time to Failure
RoHS	Restriction of Hazardous Substances
SMD	Surface Mounted Device
VHF	Very High Frequency
VSWR	Voltage Standing Wave Ratio

# 12. Revision history

**Revision history** Table 13.

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLF978P v.1	20200403	Product data sheet	-	-

#### HF / VHF power LDMOS transistor

# 13. Legal information

#### 13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition	
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.	
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.	
Product [short] data sheet	Production	This document contains the product specification.	

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <a href="http://www.ampleon.com">http://www.ampleon.com</a>.

#### 13.2 Definitions

**Draft** — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. Ampleon does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local Ampleon sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

**Product specification** — The information and data provided in a Product data sheet shall define the specification of the product as agreed between Ampleon and its customer, unless Ampleon and customer have explicitly agreed otherwise in writing. In no event however, shall an agreement be valid in which the Ampleon product is deemed to offer functions and qualities beyond those described in the Product data sheet.

#### 13.3 Disclaimers

**Maturity** — The information in this document can only be regarded as final once the relevant product(s) has passed the Release Gate in Ampleon's release process. Prior to such release this document should be regarded as a draft version.

Limited warranty and liability — Information in this document is believed to be accurate and reliable. However, Ampleon does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information. Ampleon takes no responsibility for the content in this document if provided by an information source outside of Ampleon.

In no event shall Ampleon be liable for any indirect, incidental, punitive, special or consequential damages (including - without limitation - lost profits, lost savings, business interruption, costs related to the removal or replacement of any products or rework charges) whether or not such damages are based on tort (including negligence), warranty, breach of contract or any other legal theory.

Notwithstanding any damages that customer might incur for any reason whatsoever, Ampleon's aggregate and cumulative liability towards customer for the products described herein shall be limited in accordance with the *Terms and conditions of commercial sale* of Ampleon.

Right to make changes — Ampleon reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — Ampleon products are not designed, authorized or warranted to be suitable for use in life support, life-critical or safety-critical systems or equipment, nor in applications where failure or malfunction of an Ampleon product can reasonably be expected to result in personal injury, death or severe property or environmental damage. Ampleon and its suppliers accept no liability for inclusion and/or use of Ampleon products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

**Applications** — Applications that are described herein for any of these products are for illustrative purposes only. Ampleon makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Customers are responsible for the design and operation of their applications and products using Ampleon products, and Ampleon accepts no liability for any assistance with applications or customer product design. It is customer's sole responsibility to determine whether the Ampleon product is suitable and fit for the customer's applications and products planned, as well as for the planned application and use of customer's third party customer(s). Customers should provide appropriate design and operating safeguards to minimize the risks associated with their applications and products.

Ampleon does not accept any liability related to any default, damage, costs or problem which is based on any weakness or default in the customer's applications or products, or the application or use by customer's third party customer(s). Customer is responsible for doing all necessary testing for the customer's applications and products using Ampleon products in order to avoid a default of the applications and the products or of the application or use by customer's third party customer(s). Ampleon does not accept any liability in this respect.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) will cause permanent damage to the device. Limiting values are stress ratings only and (proper) operation of the device at these or any other conditions above those given in the Recommended operating conditions section (if present) or the Characteristics sections of this document is not warranted. Constant or repeated exposure to limiting values will permanently and irreversibly affect the quality and reliability of the device.

Terms and conditions of commercial sale — Ampleon products are sold subject to the general terms and conditions of commercial sale, as published at <a href="http://www.ampleon.com/terms">http://www.ampleon.com/terms</a>, unless otherwise agreed in a valid written individual agreement. In case an individual agreement is concluded only the terms and conditions of the respective agreement shall apply. Ampleon hereby expressly objects to applying the customer's general terms and conditions with regard to the purchase of Ampleon products by customer.

#### **HF / VHF power LDMOS transistor**

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

**Export control** — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from competent authorities.

Non-automotive qualified products — Unless this data sheet expressly states that this specific Ampleon product is automotive qualified, the product is not suitable for automotive use. It is neither qualified nor tested in accordance with automotive testing or application requirements. Ampleon accepts no liability for inclusion and/or use of non-automotive qualified products in automotive equipment or applications.

In the event that customer uses the product for design-in and use in automotive applications to automotive specifications and standards, customer (a) shall use the product without Ampleon's warranty of the product for such

automotive applications, use and specifications, and (b) whenever customer uses the product for automotive applications beyond Ampleon's specifications such use shall be solely at customer's own risk, and (c) customer fully indemnifies Ampleon for any liability, damages or failed product claims resulting from customer design and use of the product for automotive applications beyond Ampleon's standard warranty and Ampleon's product specifications.

**Translations** — A non-English (translated) version of a document is for reference only. The English version shall prevail in case of any discrepancy between the translated and English versions.

#### 13.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

#### 14. Contact information

For more information, please visit: http://www.ampleon.com

For sales office addresses, please visit: <a href="http://www.ampleon.com/sales">http://www.ampleon.com/sales</a>

## **HF / VHF power LDMOS transistor**

# 15. Contents

1	Product profile
1.1	General description 1
1.2	Features and benefits
1.3	Applications
2	Pinning information 2
3	Ordering information 2
4	Limiting values 2
5	Thermal characteristics 2
6	Characteristics 3
7	Application information 5
8	Test information 6
8.1	Ruggedness in class-AB operation 6
8.2	Impedance information 6
8.3	Test circuit
8.4	Graphical data 8
8.4.1	1-Tone CW pulsed 8
9	Package outline
10	Handling information 12
11	Abbreviations12
12	Revision history 12
13	Legal information
13.1	Data sheet status
13.2	Definitions
13.3	Disclaimers
13.4	Trademarks14
14	Contact information 14
15	Contents

Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.

All rights reserved.